



Verification Futures

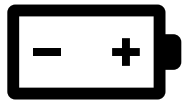
July 2025

SRAM: Dead or alive?

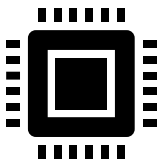
What is an SRAM?



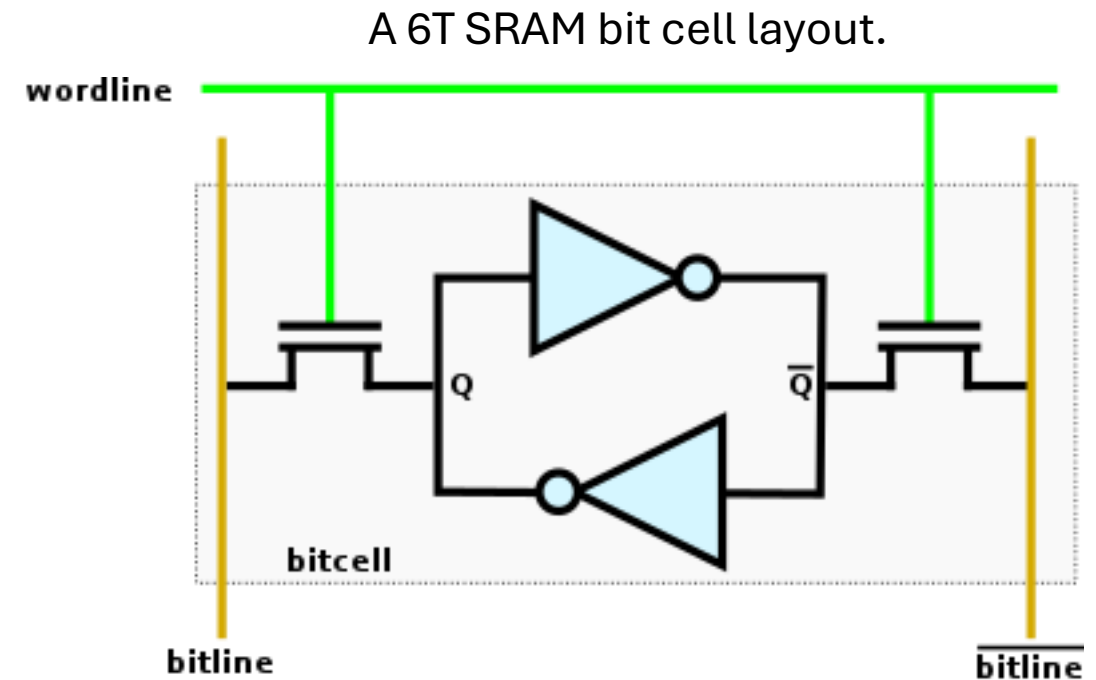
Static



Volatile

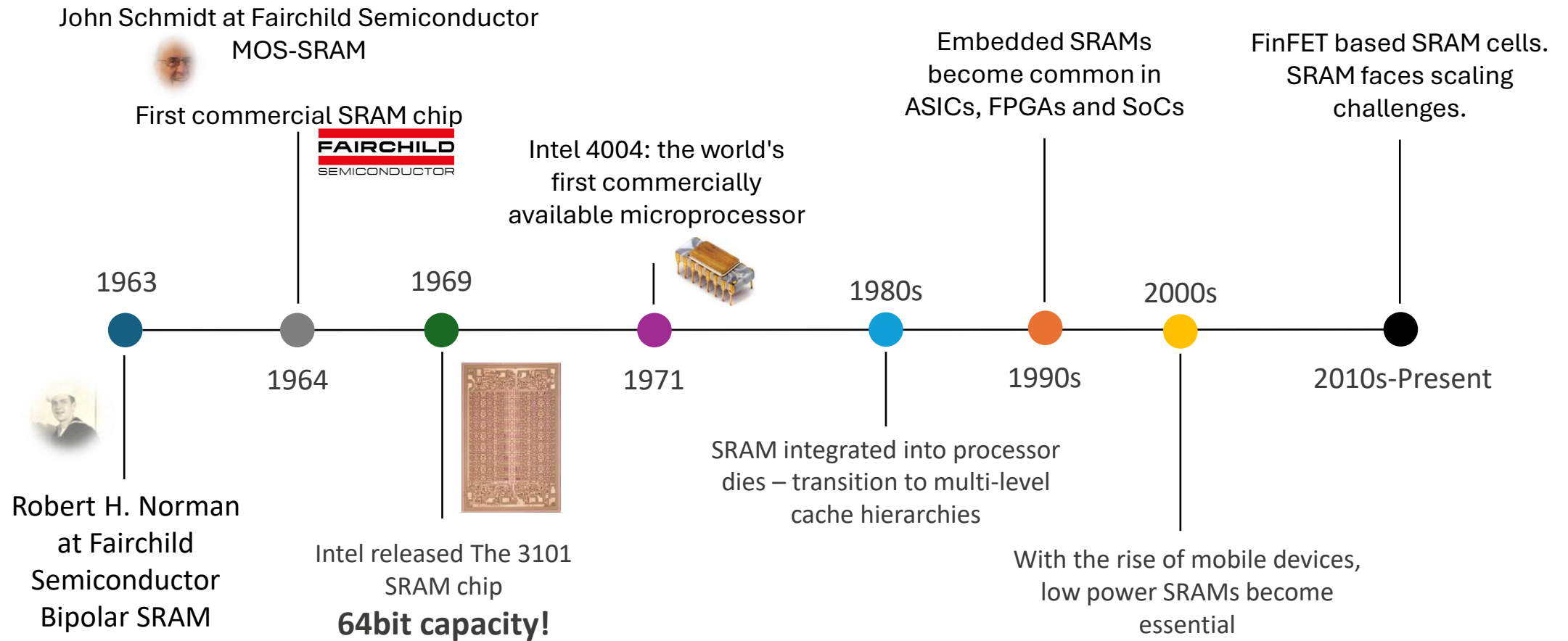


Six transistors per
bit cell



Source: https://en.wikichip.org/wiki/static_random-access_memory-google_vignette

SRAM: History and timeline



Why is it so ubiquitous?

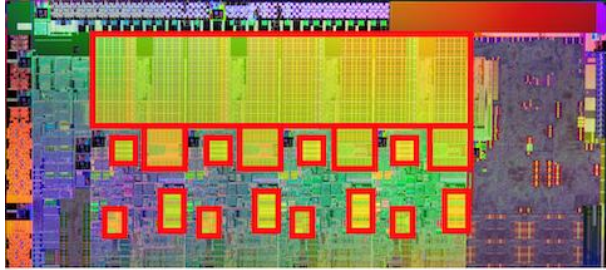
1. Best read/write latencies
2. Fully deterministic
3. Ease of integration with logic
 1. SRAM memory compiler for every process node
 2. Generate any shape and the size you want for your design

<u>Memory</u>	<u>Read latency</u>	<u>Density</u>	
SRAM	0.5-2ns	~60-120F ²	Available on every process node as part of logic foundries SRAM compilers.
DRAM	10-15ns	~6-8F ²	Special foundries that manufacture DRAM chips - currently cannot be integrated together with logic which adds additional off-chip latencies in the order of 50-100ns.
MRAM	10-35ns	~20-40F ²	Very limited foundries and process nodes.
ReRAM	10-100ns	~4F ²	Limited availability: 22nm FDSOI, 130nm etc

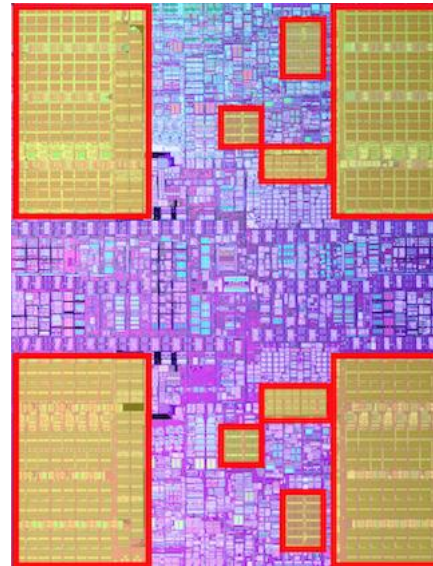
F² represents feature size relative to process node

Example designs

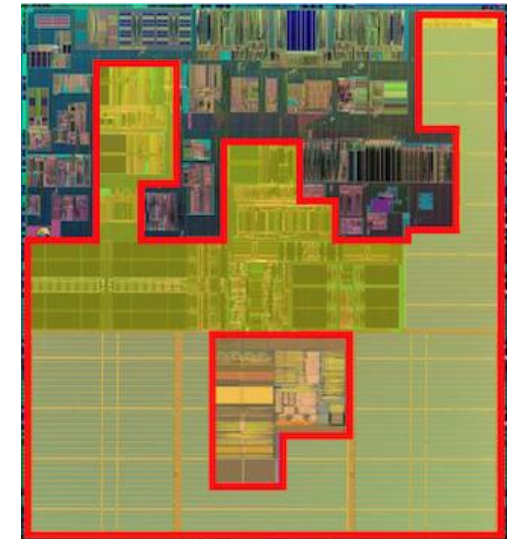
Die shots of microprocessors using a large quantity of SRAMs. Some of the smaller macros not shown.



Sandy Bridge
[32nm]



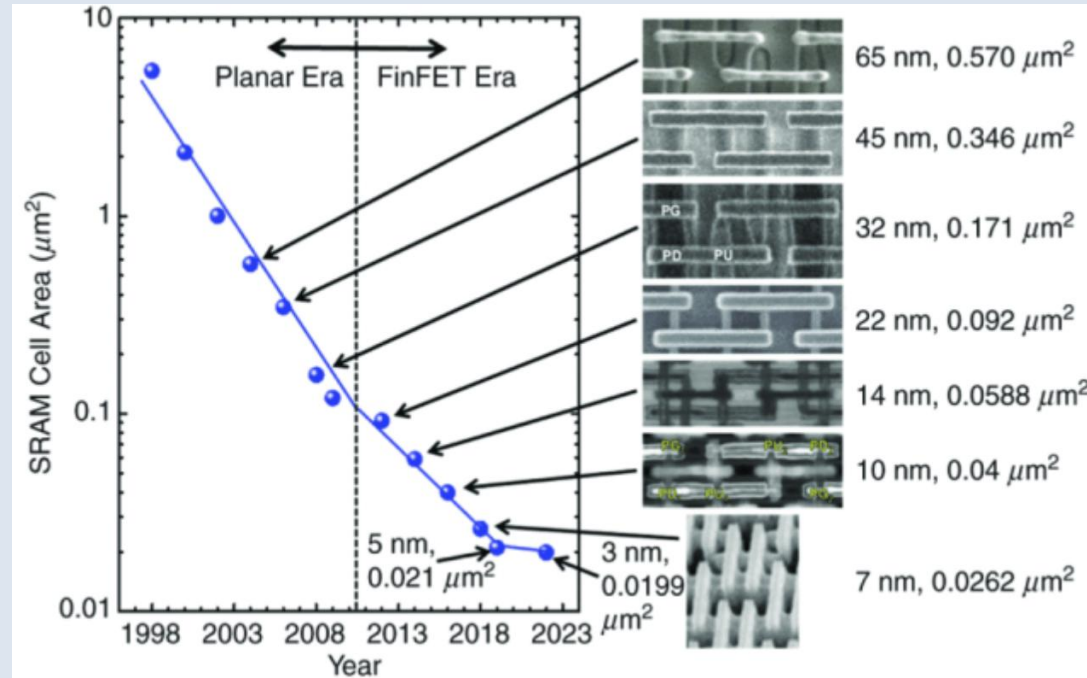
Power6
[65nm]



McKinley
[180nm]

Source: https://en.wikichip.org/wiki/static_random-access_memory-google_vignette

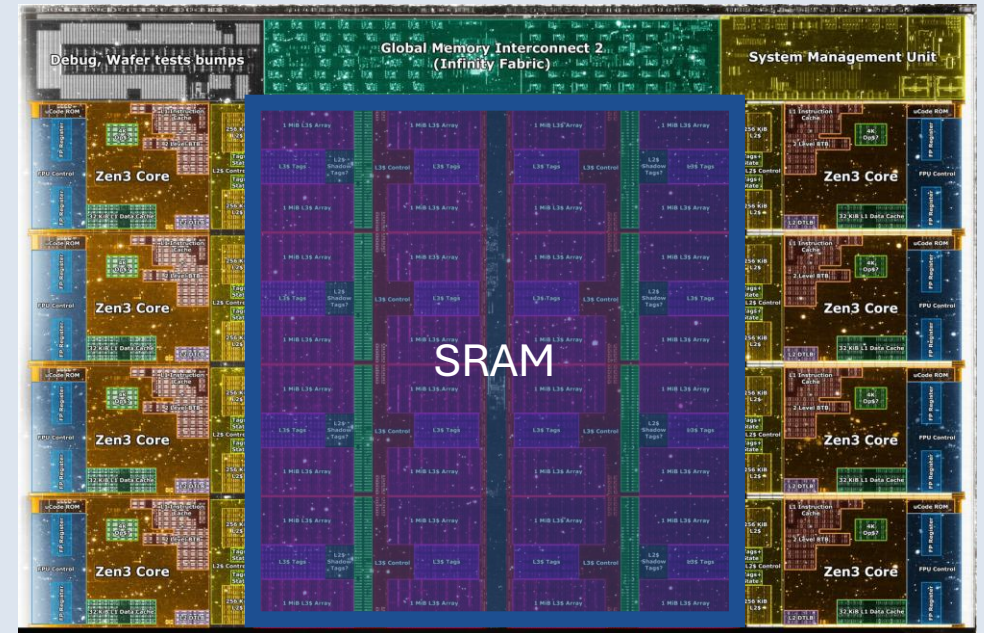
However!



Source: [H. Chang et al.](#)

SRAM scaling has *significantly* slowed down below 5nm in density and performance

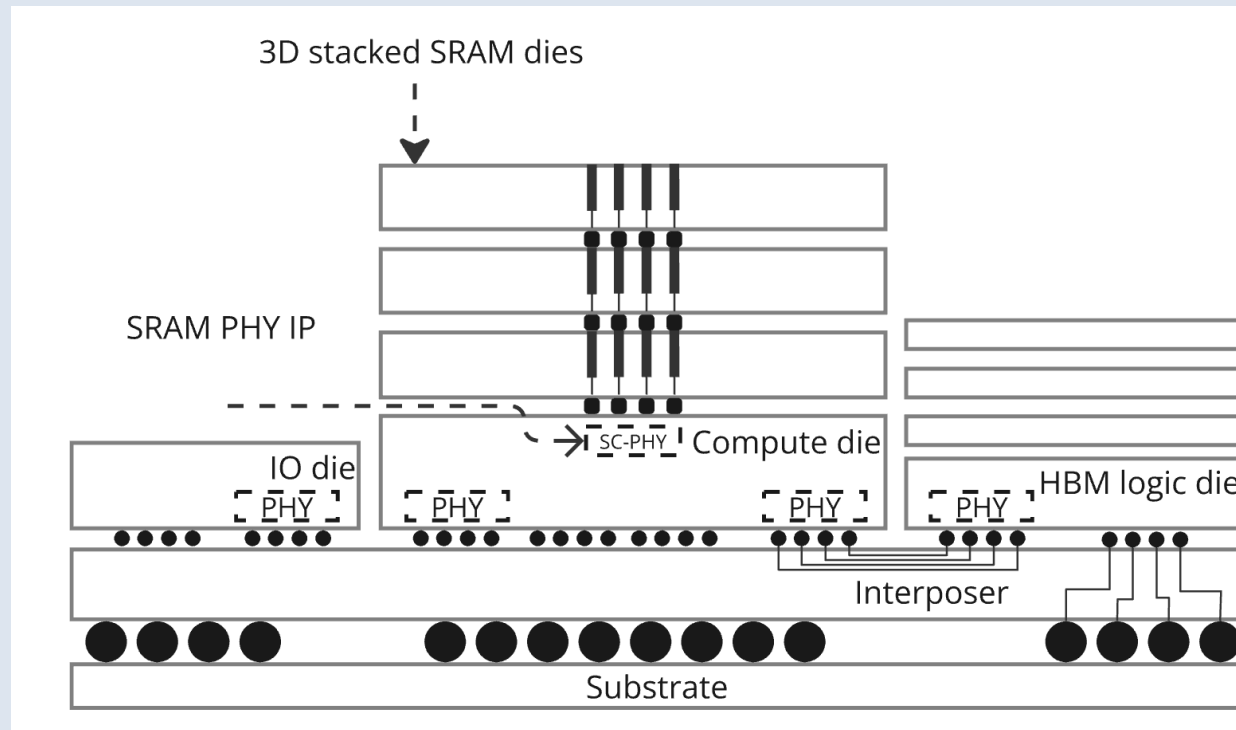
SRAM uses large chip area which could be used for logic



Source: [AMD Ryzen 5000 Zen 3 Desktop CPU Gets First High-Res Infrared Die Shot, Vermeer Fully Detailed](#)

Solution?

1. When large arrays of SRAMs are needed, put them on a separate die
2. Vertically stack them on top of compute
1. Why? Connections via silicon interposers require SerDes – latencies in the range of 50-100ns



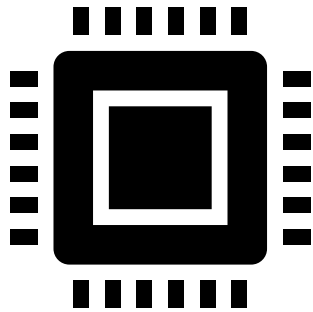
Why now?

1. Designs are hitting reticle limits
2. Advanced 3D integration with very high yields
 1. Bumpless sub 10um pitch I/Os in mass production for several years
3. Wafer costs disparity
4. Reliability/scaling issues

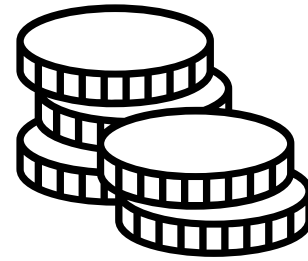
Let's dive in a bit more.

Break-even

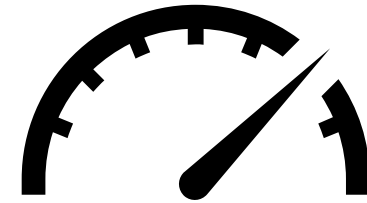
3 break-even factors to consider for switching to 3D stacked SRAMs.



PHY area



Costs



Performance

Break-even: PHY area

PHY area > SRAM macro

PHY area depends on the **number of IOs**, **process node**, the **type of bonding** and the **pitch** between the IO cells.

1MB

Hybrid bond, 9um pitch,
300 IO cells at 7nm

16MB

PHY

Break-even: Costs



Volume production costs for a **128MB** SRAM chiplet

Doesn't factor the exorbitant NRE costs!

Break-even for costs is very subjective.

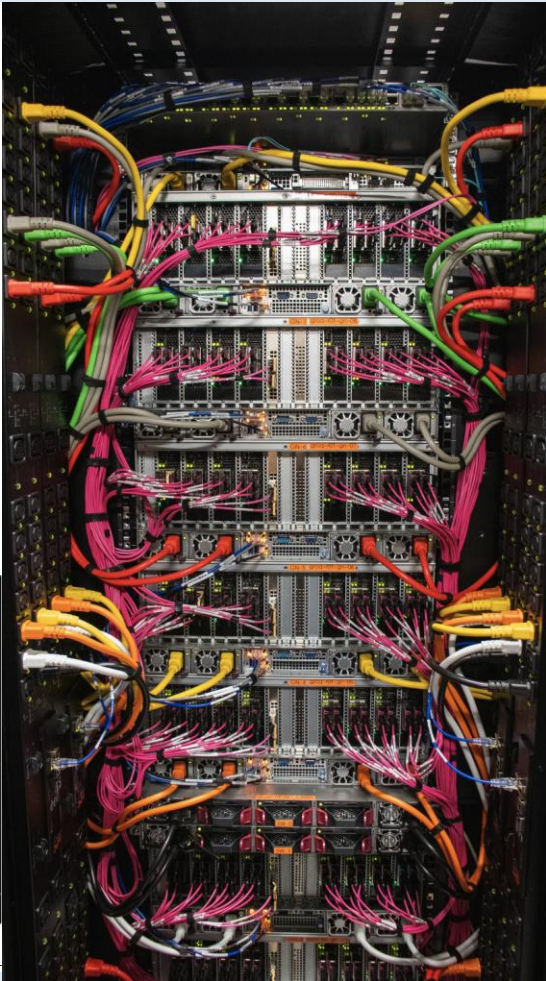
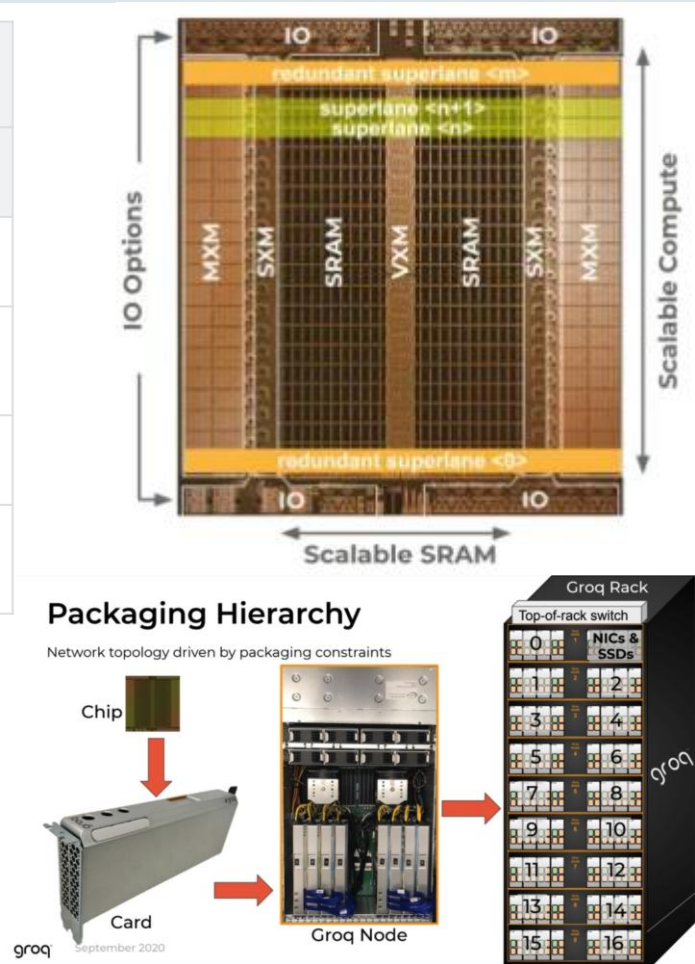
Break-even: Performance

Need to measure system level performance. Factors to consider include **F_{max}** improvements due to smaller compute die, **lower latencies** within the compute die, **higher latencies** to off chip SRAMs and **higher SRAM capacity**.

Example: AI inference

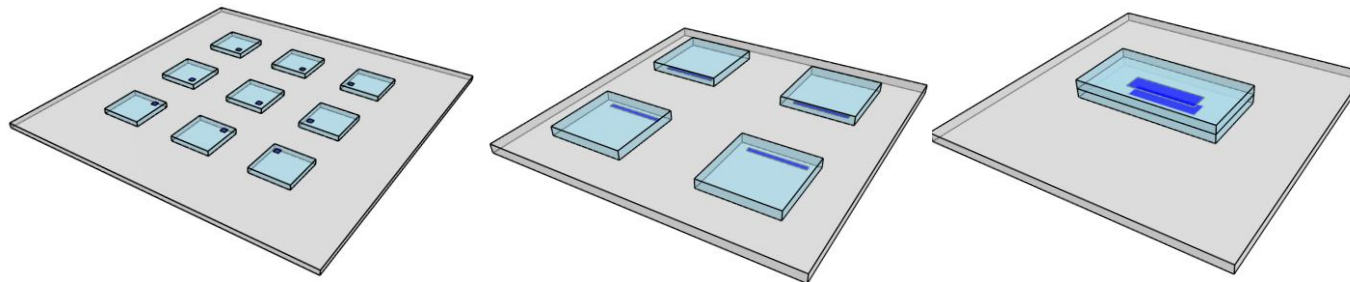
AI Model size	Memory		#Chips	Optical cables	
	Size	Stack		#Number	Miles
7B	16GB	2D	70	315	1.9
		3D	16	70	0.4
10T	20TB	2D	95,325	428962	2659
		3D	16,850	75825	470

A memory stacked approach can save 4-10x number of chip modules or optical cables for the same AI model.



SRAM chiplets: configurations

Products	Small	Medium	Large
Memory	16MB	64MB	128MB
Chiplet Area	4.5mm ²	16.8mm ²	33.7mm ²
I/Os	256	512	1024
Macro area	0.02mm ²	0.05mm ²	0.05mm ²
Bandwidth	128Gb/s	256Gb/s	512Gb/s
Process	7nm		
Bond pitch	9um		



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Thank you

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